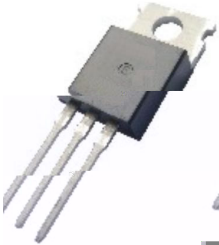
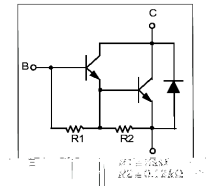


Rev. H Oct.-2018

TO-220 NPN Silicon NPN transistor in a TO-220 Plastic Package.

TIP127
 Complement to TIP127.

Medium power linear switching applications.

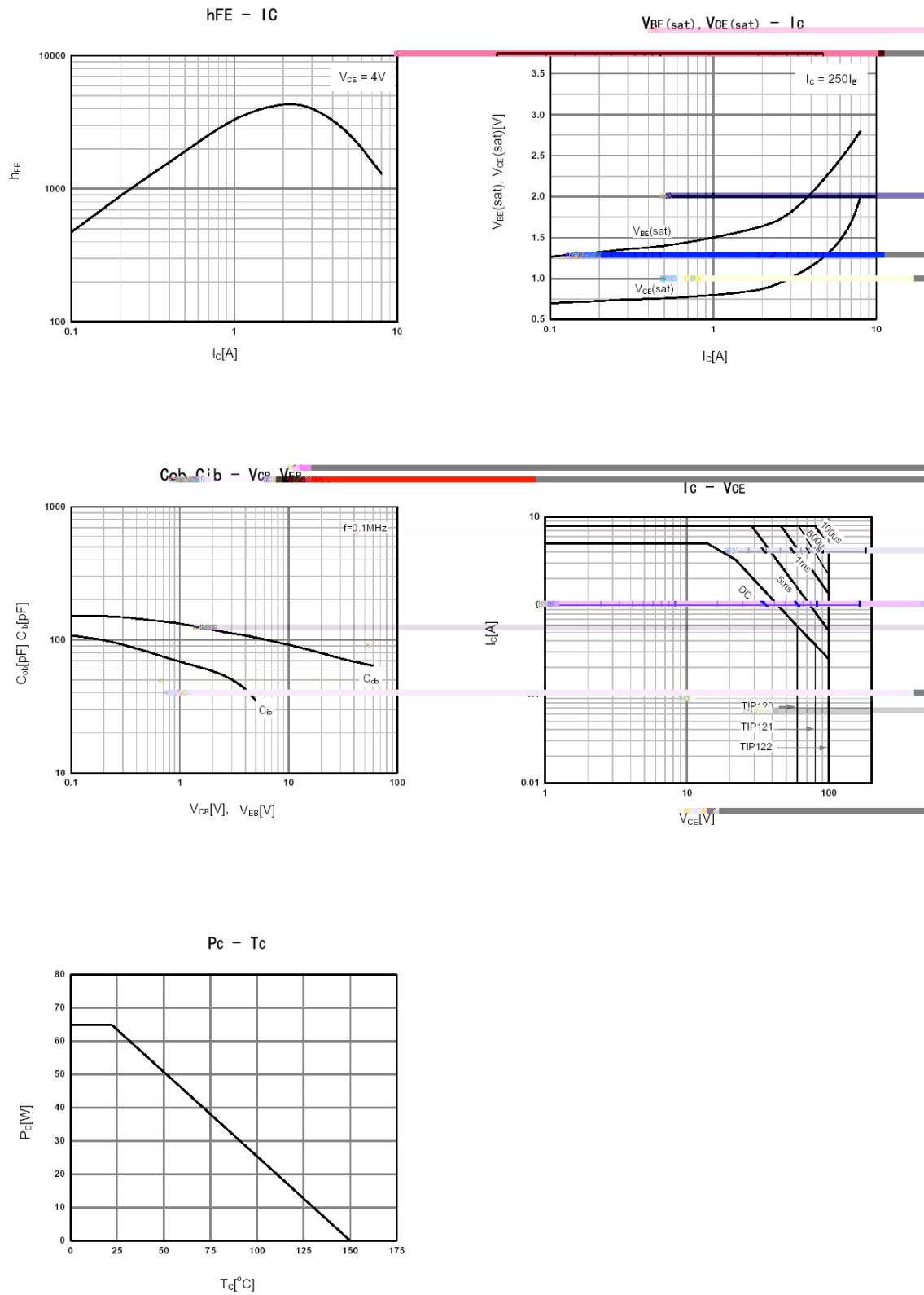


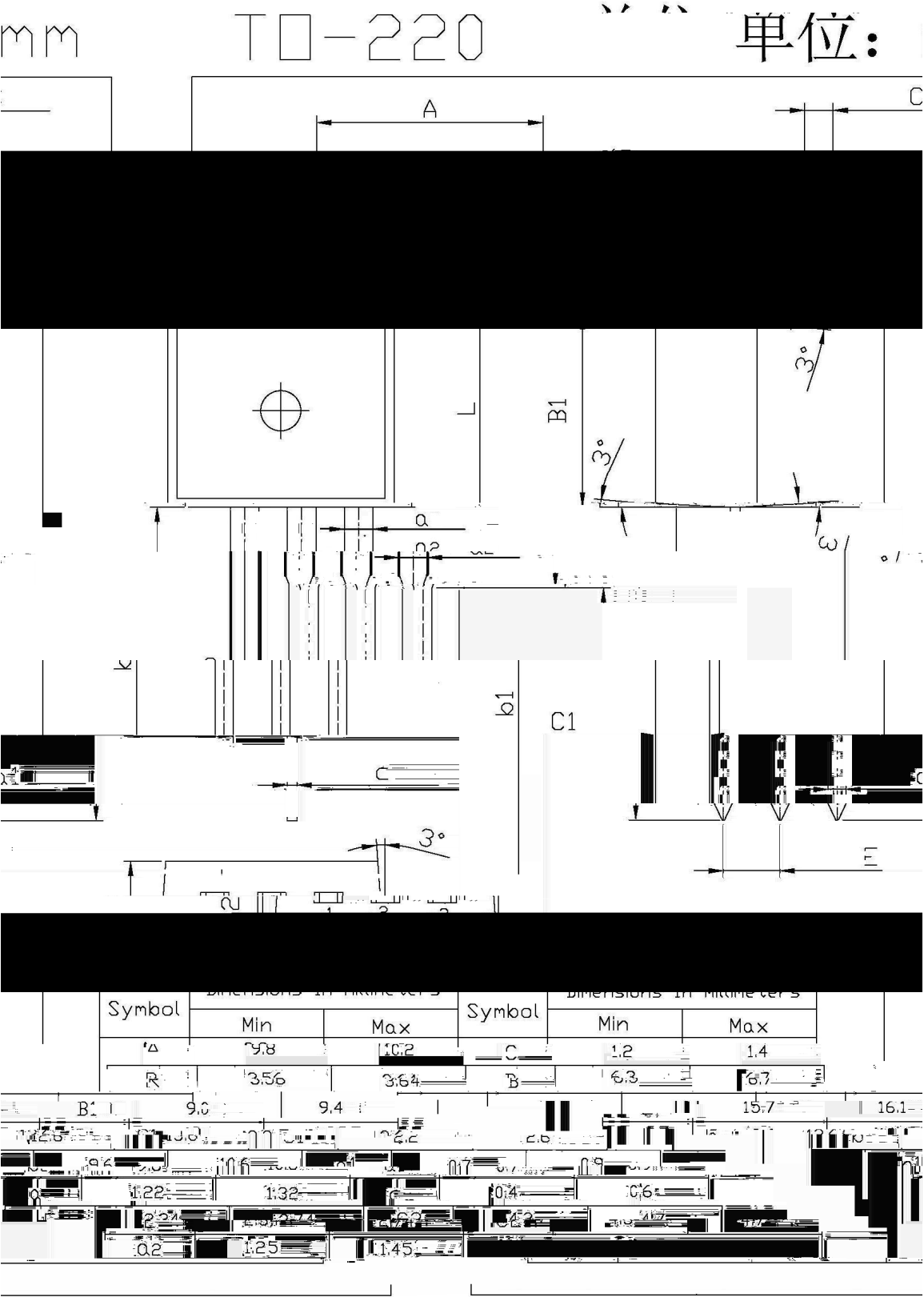
PIN1 Base PIN 2 Collector PIN 3 Emitter

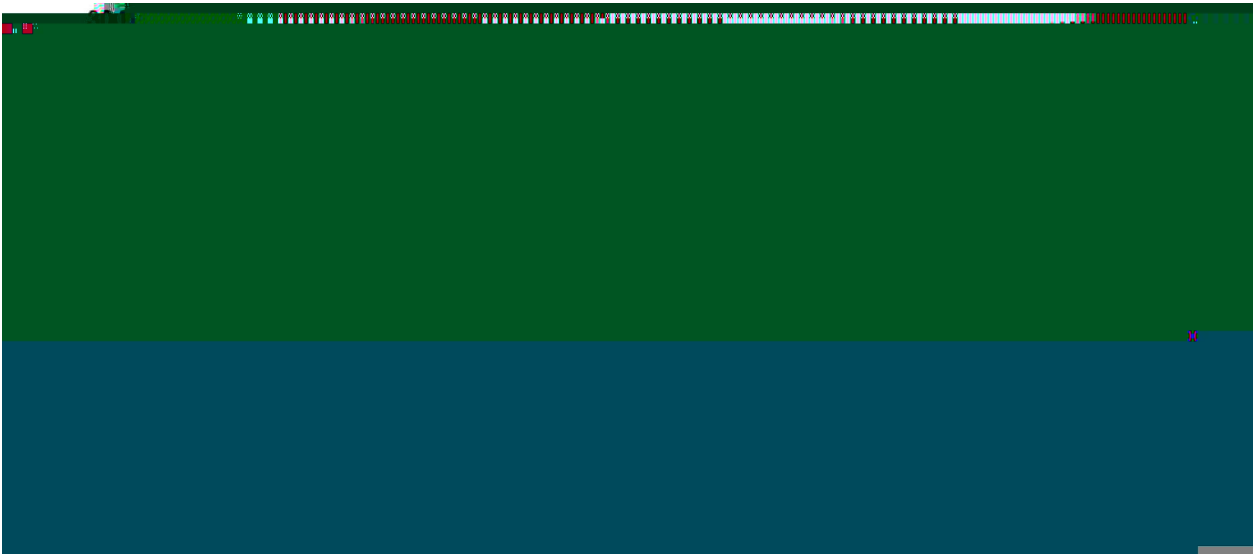
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	100	V
Collector to Emitter Voltage	V_{CEO}	100	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	5.0	A
Peak Collector Current	I_{CP}	8.0	A
Base Current - Continuous	I_B	120	mA
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	65	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=100\text{mA}$ $I_B=0$	100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=50\text{V}$ $I_B=0$			0.5	mA
Collector Cut-Off Current	I_{CBO}	$V_{CB}=100\text{V}$ $I_E=0$			0.2	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=5.0\text{V}$ $I_C=0$			2.0	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=3.0\text{V}$ $I_C=0.5\text{A}$	1000			
	$h_{FE(2)}$	$V_{CE}=3.0\text{V}$ $I_C=3.0\text{A}$	1000			
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=3.0\text{A}$ $I_B=12\text{mA}$			2.0	V
	$V_{CE(sat)(2)}$	$I_C=5.0\text{A}$ $I_B=20\text{mA}$			4.0	V
Base to Emitter Voltage	V_{BE}	$I_C=3.0\text{A}$ $V_{CE}=3.0\text{V}$			2.5	V
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$ $I_E=0$ $f=0.1\text{MHz}$			200	pF







- 1

25 150

60 90sec;

2

255±5

5±0.5sec;

3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units 包装数量			Dimension 包装尺寸 (unit: mm ³)
封装形式	只 袋	袋 盒	只 盒	